rinneu rages—4				EEC309
(Following Paper ID	and Roll No. t	to be fille	ed in your	Answer Book)
PAPER ID: 0321	Roll No.			

B. Tech.

(SEM. III) ODD SEMESTER THEORY EXAMINATION 2010-11

ANALOG AND DIGITAL ELECTRONICS

Time : 3 Hours

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Total Marks : 100

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Note : Attempt all questions. All questions carry equal marks.

- 1. Attempt any **four** parts of the following : (5×4=20)
 - (a) Explain the operation of a LED with the help of necessary diagrams. List the materials used for constructing LED.
 Give the advantages and disadvantages of LED.
 - (b) Explain the forward and reverse characteristics of a Tunnel diode and explain the tunneling operation.
 - (c) Explain the characteristics of a varactor diode and mention how it can be used in a resonant circuit. Also list some of the applications of the varactor diode.
 - (d) Explain the construction, operation and I-V characteristics of a Schottky diode. Also give its equivalent circuit diagram and circuit symbol.
 - (e) With the help of a neatly labeled circuit diagram explain the switching operation of a transistor. Also give the switching waveforms.

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- (f) Define and explain the following terms in case of a photo detector :
 - (i) Responsivity
 - (ii) Quantum Efficiency
 - (iii) Directivity
 - (iv) Dark Current.

2. Attempt any two parts of the following : (10×2=20)

- (a) Why h-parameters could not be used for high frequency analysis of the transistors? Give the hybrid- π equivalent circuit of a Bipolar Junction Transistor, explaining the significance of the terms appearing in the circuit. Define the following — f_{α} , f_{β} and f_{T} and derive the relationship between f_{α} and f_{β} .
- (b) Give the high frequency small-signal circuit of a MOSFET with load resistance showing the effect of Miller capacitance. Also derive an expression for the Miller Capacitance and cut-off frequency (f_τ).
- (c) What are the general properties of Negative feedback ? And explain how negative feedbacks can be used for input resistance, output resistance, and bandwidth stability.
- 3. Attempt any two parts of the following: (10×2=20)
 - (a) Explain the Barkhausen criteria for oscillators. And also derive the necessary conditions required for oscillations.
 What are the factors on the basis of which oscillators are classified ?

- (b) Design an RC phase shift oscillators using BJT for a frequency of 1 kHz. The stability factor S ≤ 8. Given that V_{cc} = 10 V. The transistor has h-parameters as follows h_x = 1kΩ, h_y = 50, h_y = h_y = 0.
- (c) Explain the operation of a Wien-Bridge oscillator and derive the necessary condition for oscillation. Give the equivalent circuit of a crystal and give the advantages of a crystal oscillator.
- 4. Attempt any four parts of the following: (5×4=20)
 - (a) Define combinational circuit. Realize the following expression f (A, B, C) = Σm (0, 2, 4, 6) using a 4 : 1 multiplexer.
 - (b) Explain the difference between Latch and Flip-Flop. Explain how a D Flip-Flop is obtained from a JK Flip-Flop.
 - (c) Design a 3-bit Bi-Directional Shift resistor using JK Flip-Flop.
 - (d) What is a universal shift register ? Explain its operation with the help of a logic diagram showing all the necessary signals.
 - (e) Differentiate between synchronous and asynchronous counter. Give the logic diagram of a BCD counter.
 - (f) Explain the operation of a Johnson counter using D Flip-Flop.
- 5. Attempt any four parts of the following: (5×4=20)
 - (a) Give the circuit diagram of a Non-inverting Schmitt Trigger and derive the expression for Hystersis voltage.

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- (b) Explain the operation of a Astable Multivibrator circuit using an Op-Amp. Also derive the expression for cut off frequency.
- (c) Give the functional block diagram of timer IC 555 and explain how it can be used to obtain a Monostable Multivibrator.
- (d) Distinguish between A/D and D/A converters. Explain the operation of any one of them.
- (e) Give the circuit diagram of a sample and hold circuit and explain its operation.
- (f) Explain the procedure for obtaining a 32 × 4 memory using 16 × 4 memory chips. Also show the necessary circuit diagram.